

# PMBFJ108; PMBFJ109; PMBFJ110 N-channel junction FETs

Rev. 4 — 20 September 2011

**Product data sheet** 

#### **Product profile** 1.

### 1.1 General description

Symmetrical N-channel junction FETs in a SOT23 package.

### 1.2 Features and benefits

- High-speed switching
- Interchangeability of drain and source connections
- Low  $R_{DSon}$  at zero gate voltage (< 8  $\Omega$  for PMBFJ108).

### 1.3 Applications

- Analog switches
- Choppers and commutators
- Audio amplifiers.

#### **Pinning information** 2.

Table 1.	Pinning		
Pin	Description <sup>[1]</sup>	Simplified outline	Symbol
1	drain	□3	
2	source		
3	gate		$3 \xrightarrow{1} 2$ sym053

[1] Drain and source are interchangeable.



**N-channel junction FETs** 

## 3. Ordering information

Table 2.         Ordering information					
Type number	Package				
	Name	Description	Version		
PMBFJ108	-	plastic surface mounted package; 3 leads	SOT23		
PMBFJ109					
PMBFJ110					

## 4. Marking

Table 3. Marking	
Type number	Marking code <sup>[1]</sup>
PMBFJ108	38*
PMBFJ109	39*
PMBFJ110	40*

[1] \* = p: Made in Hong Kong

\* = t: Made in Malaysia

\* = W: Made in China

## 5. Limiting values

### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage (DC)		-	±25	V
V <sub>GSO</sub>	gate-source voltage		-	-25	V
V <sub>GDO</sub>	gate-drain voltage		-	-25	V
l <sub>G</sub>	forward gate current (DC)		-	50	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} = 25 \ ^{\circ}C$	<u>[1]</u> -	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

[1] Mounted on an FR4 printed-circuit board.

## 6. Thermal characteristics

Table 5.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		<u>[1]</u> 500	K/W

[1] Mounted on an FR4 printed-circuit board.

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## 7. Static characteristics

Static characteristics					
Parameter	Conditions	Min	Тур	Max	Unit
gate-source leakage current	$V_{GS} = -15 \text{ V};  V_{DS} = 0 \text{ V}$	-	-	-3	nA
drain-source cut-off current	$V_{GS}$ = -10 V; $V_{DS}$ = 5 V	-	-	3	nA
drain-source leakage current					
PMBFJ108	$V_{GS} = 0 V; V_{DS} = 15 V$	80	-	-	mA
PMBFJ109	$V_{GS} = 0 V; V_{DS} = 15 V$	40	-	-	mA
PMBFJ110	$V_{GS} = 0 V; V_{DS} = 15 V$	10	-	-	mA
gate-source breakdown voltage	$I_G = -1 \ \mu A; \ V_{DS} = 0 \ V$	-	-	-25	V
gate-source cut-off voltage					
PMBFJ108	$I_D = 1 \ \mu A; \ V_{DS} = 5 \ V$	-10	-	-3	V
PMBFJ109	$I_D = 1 \ \mu A; \ V_{DS} = 5 \ V$	-6	-	-2	V
PMBFJ110	$I_{D} = 1 \ \mu A; \ V_{DS} = 5 \ V$	-4	-	-0.5	V
drain-source on-state resistance					
PMBFJ108	$V_{GS} = 0 V; V_{DS} = 0.1 V$	-	-	8	Ω
PMBFJ109	$V_{GS} = 0 V; V_{DS} = 0.1 V$	-	-	12	Ω
PMBFJ110	$V_{GS} = 0 V; V_{DS} = 0.1 V$	-	-	18	Ω
	Parametergate-source leakage currentdrain-source cut-off currentdrain-source leakage currentPMBFJ108PMBFJ109PMBFJ110gate-source breakdown voltagegate-source cut-off voltagePMBFJ108PMBFJ109PMBFJ109PMBFJ109PMBFJ109PMBFJ109PMBFJ110drain-source on-state resistancePMBFJ108PMBFJ109PMBFJ109	Parameter         Conditions           gate-source leakage current $V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}$ drain-source cut-off current $V_{GS} = -10 \text{ V}; V_{DS} = 5 \text{ V}$ drain-source leakage current         PMBFJ108           PMBFJ109 $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ PMBFJ109 $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ PMBFJ110 $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ gate-source breakdown voltage $I_G = -1 \mu A; V_{DS} = 0 \text{ V}$ gate-source cut-off voltage $I_D = 1 \mu A; V_{DS} = 5 \text{ V}$ PMBFJ108 $I_D = 1 \mu A; V_{DS} = 5 \text{ V}$ PMBFJ109 $I_D = 1 \mu A; V_{DS} = 5 \text{ V}$ PMBFJ109 $I_D = 1 \mu A; V_{DS} = 5 \text{ V}$ PMBFJ109 $I_D = 1 \mu A; V_{DS} = 5 \text{ V}$ PMBFJ109 $V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$ PMBFJ108 $V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$	Parameter         Conditions         Min           gate-source leakage current $V_{GS} = -15 V$ ; $V_{DS} = 0 V$ -           drain-source cut-off current $V_{GS} = -10 V$ ; $V_{DS} = 5 V$ -           drain-source leakage current         V         S         -           PMBFJ108 $V_{GS} = 0 V$ ; $V_{DS} = 15 V$ 80           PMBFJ109 $V_{GS} = 0 V$ ; $V_{DS} = 15 V$ 40           PMBFJ110 $V_{GS} = 0 V$ ; $V_{DS} = 15 V$ 10           gate-source breakdown voltage $I_G = -1 \mu A$ ; $V_{DS} = 0 V$ -           gate-source cut-off voltage         -         -           PMBFJ108 $I_D = 1 \mu A$ ; $V_{DS} = 5 V$ -10           PMBFJ109 $I_D = 1 \mu A$ ; $V_{DS} = 5 V$ -6           PMBFJ110 $I_D = 1 \mu A$ ; $V_{DS} = 5 V$ -4           drain-source on-state resistance         -         -           PMBFJ108 $V_{GS} = 0 V$ ; $V_{DS} = 0.1 V$ -           PMBFJ109 $V_{GS} = 0 V$ ; $V_{DS} = 0.1 V$ -	ParameterConditionsMinTypgate-source leakage current $V_{GS} = -15 V$ ; $V_{DS} = 0 V$ drain-source cut-off current $V_{GS} = -10 V$ ; $V_{DS} = 5 V$ drain-source leakage currentVGS = 0 V; $V_{DS} = 15 V$ 80-PMBFJ108 $V_{GS} = 0 V$ ; $V_{DS} = 15 V$ 40-PMBFJ109 $V_{GS} = 0 V$ ; $V_{DS} = 15 V$ 40-pMBFJ110 $V_{GS} = 0 V$ ; $V_{DS} = 15 V$ 10-gate-source breakdown voltage $I_G = -1 \mu A$ ; $V_{DS} = 0 V$ gate-source cut-off voltage $I_G = 1 \mu A$ ; $V_{DS} = 5 V$ -10-PMBFJ108 $I_D = 1 \mu A$ ; $V_{DS} = 5 V$ -6-PMBFJ109 $I_D = 1 \mu A$ ; $V_{DS} = 5 V$ -4-drain-source on-state resistancePMBFJ109 $V_{GS} = 0 V$ ; $V_{DS} = 0.1 V$ PMBFJ109 $V_{GS} = 0 V$ ; $V_{DS} = 0.1 V$	ParameterConditionsMinTypMaxgate-source leakage current $V_{GS} = -15 V; V_{DS} = 0 V$ 3drain-source cut-off current $V_{GS} = -10 V; V_{DS} = 5 V$ 3drain-source leakage currentVGS = 0 V; V_{DS} = 15 V80PMBFJ108 $V_{GS} = 0 V; V_{DS} = 15 V$ 80PMBFJ109 $V_{GS} = 0 V; V_{DS} = 15 V$ 40PMBFJ110 $V_{GS} = 0 V; V_{DS} = 15 V$ 10gate-source breakdown voltage $I_G = -1 \mu A; V_{DS} = 0 V$ 25gate-source cut-off voltage $I_D = 1 \mu A; V_{DS} = 5 V$ -103PMBFJ108 $I_D = 1 \mu A; V_{DS} = 5 V$ -6-2-2PMBFJ109 $I_D = 1 \mu A; V_{DS} = 5 V$ -4-0.5-0.5drain-source on-state resistancePMBFJ108 $V_{GS} = 0 V; V_{DS} = 0.1 V$ 8PMBFJ109 $V_{GS} = 0 V; V_{DS} = 0.1 V$ 12

## 8. Dynamic characteristics

#### Table 7. Dynamic characteristics

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
C <sub>iss</sub> input capacitance	$V_{DS} = 0 V; V_{GS} = -10 V; f = 1 MHz$		-	15	30	pF	
		$V_{DS}$ = 0 V; $V_{GS}$ = 0 V; f = 1 MHz; $T_{amb}$ = 25 °C		-	50	85	pF
C <sub>rss</sub>	feedback capacitance	$V_{DS} = 0 V; V_{GS} = -10 V; f = 1 MHz$		-	8	15	pF
Switching	g times (see <mark>Figure 2</mark> )						
t <sub>d</sub>	delay time		[1]	-	2	-	ns
t <sub>on</sub>	turn-on time		[1]	-	4	-	ns
t <sub>s</sub>	storage time		[1]	-	4	-	ns
t <sub>off</sub>	turn-off time		[1]	-	6	-	ns

[1] Test conditions for switching times are as follows:

 $V_{DD}$  = 1.5 V,  $V_{GS}$  = 0 V to  $V_{GSoff}$  (all types);

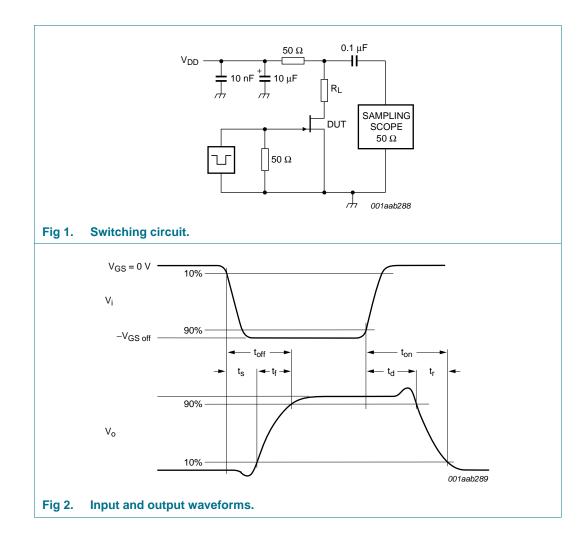
 $V_{GSoff}$  = -12 V,  $R_L$  = 100  $\Omega$  (PMBFJ108);

 $V_{GSoff}$  = -7 V,  $R_L$  = 100  $\Omega$  (PMBFJ109);

 $V_{GSoff}$  = -5 V,  $R_L$  = 100  $\Omega$  (PMBFJ110).

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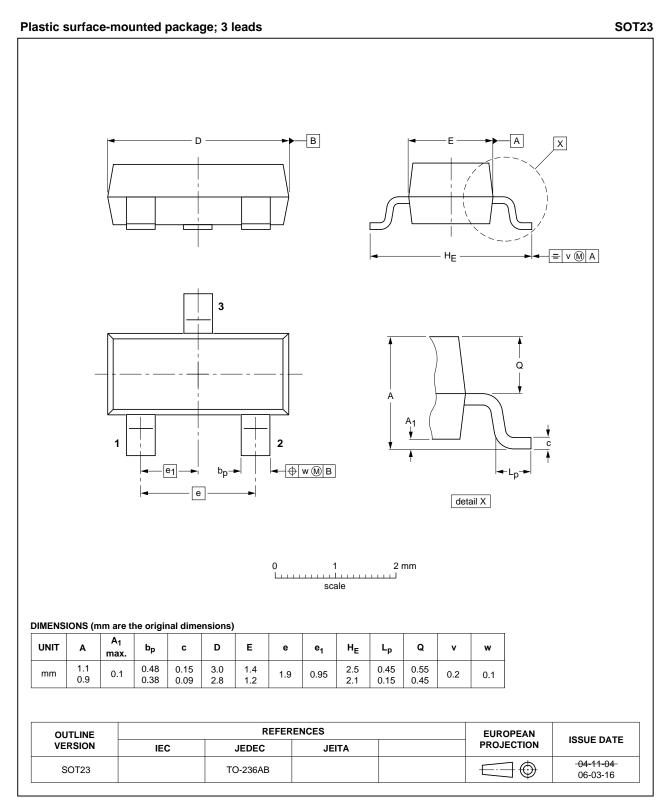


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## 9. Package outline



### Fig 3. Package outline.

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## **10. Revision history**

Table 8.Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBFJ108_109_110 v.4	20110920	Product data sheet	-	PMBFJ108_109_110 v.3
Modifications:	guidelines o Legal texts	of NXP Semiconductors.	ne new company n	comply with the new identity ame where appropriate. atest version.
PMBFJ108_109_110 v.3 (9397 750 13401)	20040804	Product data sheet	-	PMBFJ108_109_110_CNV v.2
PMBFJ108_109_110_CNV v.2	19971201	Product specification	-	-

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## 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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